## Supporting Information

## Single-phase Alkylammonium Cesium Lead Iodide Quasi-2D Perovskite for Color-tunable and Spectrum-stable Red LEDs

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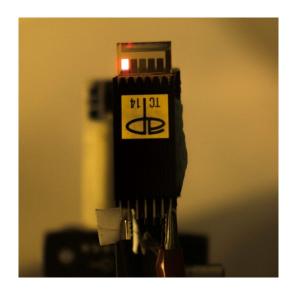
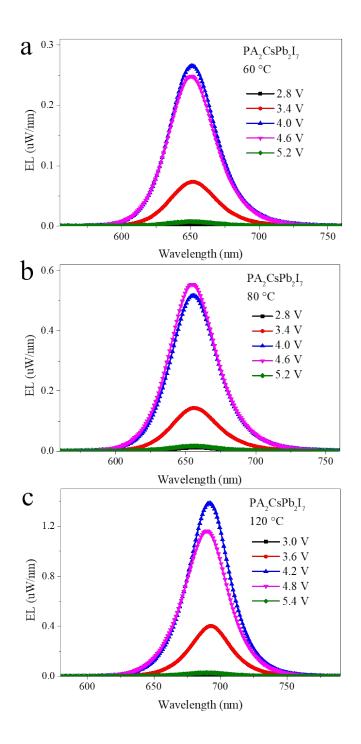
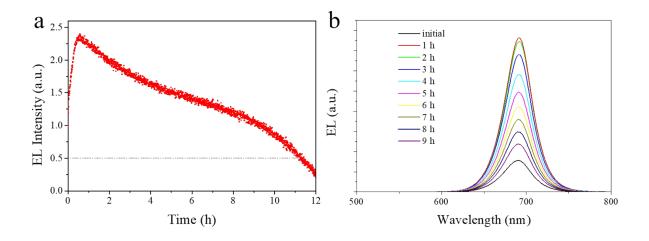


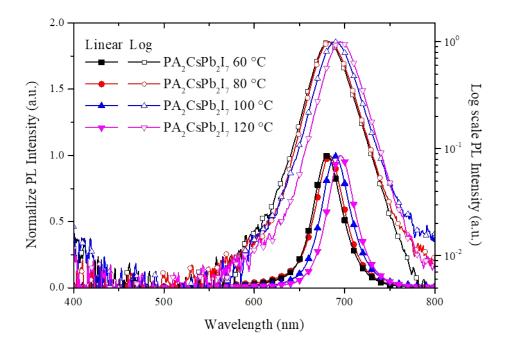
Figure S1. Photograph of PA<sub>2</sub>CsPb<sub>2</sub>I<sub>7</sub> PeLED (100 °C) under operation.



**Figure S2**. Voltage-dependent EL spectra of PA<sub>2</sub>CsPb<sub>2</sub>I<sub>7</sub> PeLEDs annealed at a) 60 °C, b) 80 °C, and c) 120 °C.



**Figure S3**. Device stability test of  $PA_2CsPb_2I_7$  PeLEDs annealed 120 °C: a) EL intensity (I/I<sub>0</sub>) against time; b) EL spectrum measured at different operation time. Measurement was carried out at a fix current density of 10 mA/cm<sup>2</sup> in glove box without encapsulation.



**Figure S4**. PL of  $PA_2CsPb_2I_7$  thin films in linear and log scale.

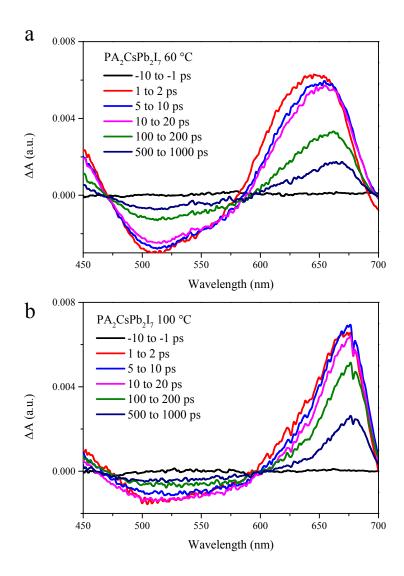


Figure S5. TA spectra of PA<sub>2</sub>CsPb<sub>2</sub>I<sub>7</sub> thin films annealed at 60 and 100 °C.

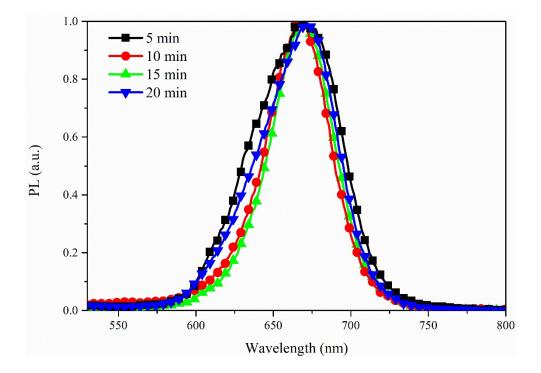
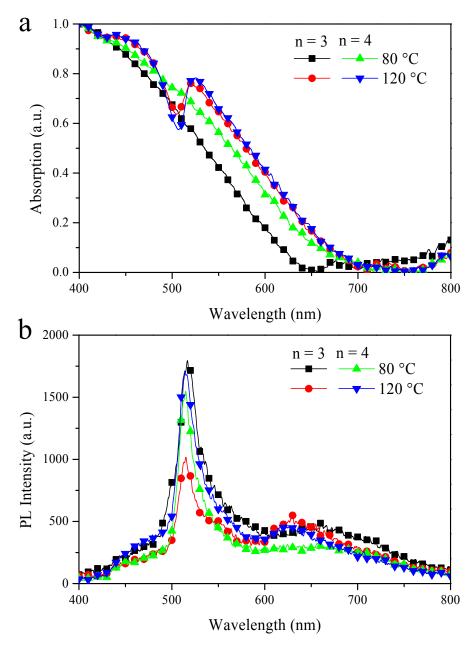
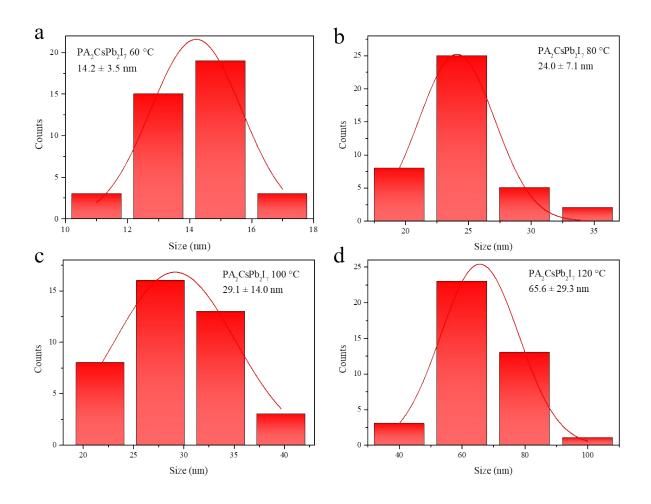


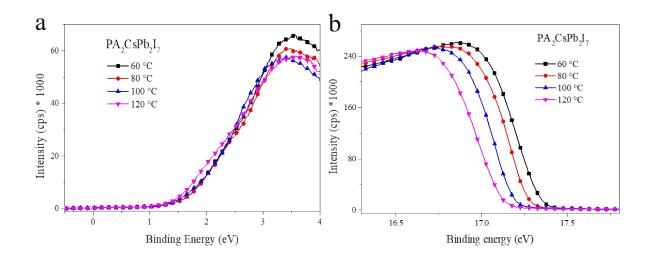
Figure S6. PL spectra of PA<sub>2</sub>CsPb<sub>2</sub>I<sub>7</sub> PeLEDs annealed 100 °C with different annealing times.



**Figure S7**. Absorption (a) and PL (b) spectra of  $PA_2Cs_2Pb_3I_{10}$  (n = 3) and  $PA_2Cs_3Pb_4I_{13}$  (n = 4) thin films.



**Figure S8**. Histograms of grain size distribution for  $PA_2CsPb_2I_7$  thin films annealed at 60 °C, 80 °C, 100 °C, and 120 °C, respectively. The grain size was measured by the grain edge length in the SEM images.



**Figure S9**. Ultraviolet photoelectron spectroscopy (UPS) results of  $PA_2CsPb_2I_7$  thin films (60 °C, 80 °C, 100 °C, and 120 °C) on ITO substrate. Valance band maximum of  $PA_2CsPb_2I_7$  gradually reduced with increased annealing temperature.

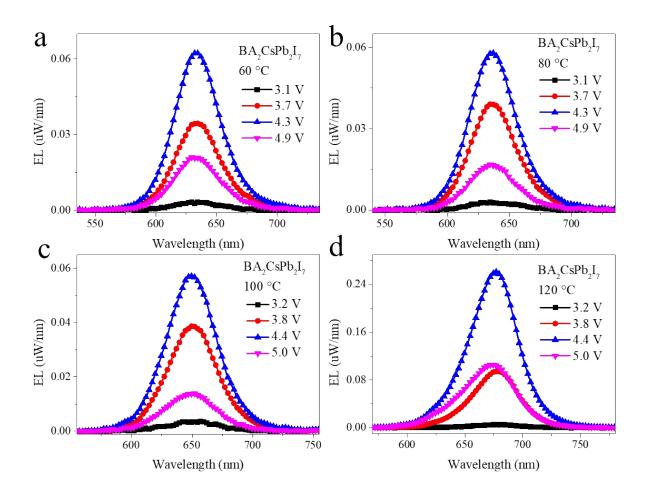


Figure S10. Voltage-dependent EL spectra of  $BA_2CsPb_2I_7$  PeLEDs (60 °C (a), 80 °C (b), 100

°C (c), and 120 °C (d)).

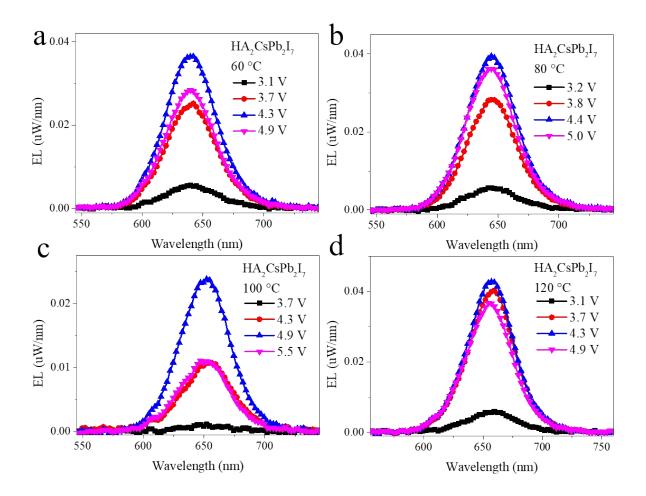


Figure S11. Voltage-dependent EL spectra of  $HA_2CsPb_2I_7$  PeLEDs (60 °C (a), 80 °C (b), 100 °C (c), and 120 °C (d)).

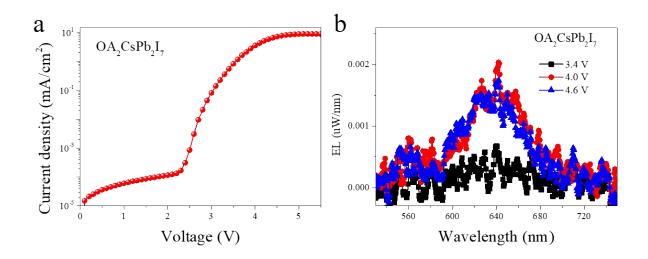


Figure S12. a) Current density-voltage curve and b) EL spectra of  $(C_6H_{13}NH_3)_2CsPb_2I_7$ (OA<sub>2</sub>CsPb<sub>2</sub>I<sub>7</sub>) PeLEDs.